METHOD AND APPARATUS FOR SHAPING GAS PROFILE NEAR BEVEL EDGE

Abstract

A method for etching a bevel edge of a substrate in a processing chamber is provided. The method includes flowing an inert gas into a center region of the processing chamber defined above a center region of the substrate and flowing a mixture of an inert gas and a processing gas over an edge region of the substrate. The method farther includes striking a plasma in the edge region, wherein the flow of the inert gas and the flow of the mixture maintain a mass fraction of the processing gas substantially constant. A processing chamber configured to clean a bevel edge of a substrate is also provided.

Figure 3